

NJ36D Process

Silicon Junction Field-Effect Transistor

- Monolithic Dual Construction
- High Frequency Amplifier
- Low-Noise Amplifier

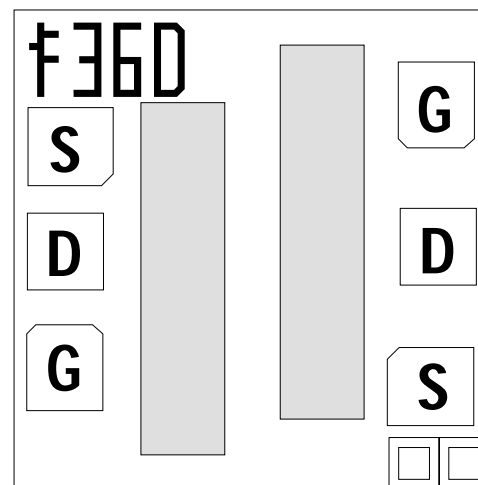
Absolute maximum ratings at TA = 25 °C

Gate Current, I _G	10 mA
Operating Junction Temperature, T _J	+150°C
Storage Temperature, T _S	- 65°C to +175°C

Devices in this Databook based on the NJ36D Process.

Datasheet

2N5911, 2N5912
IFN5911, IFN5912



Die Size = 0.026" X 0.026"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

At 25°C free air temperature:

Static Electrical Characteristics

		NJ36D Process						
		Min	Typ	Max	Unit	Test Conditions		
Gate Source Breakdown Voltage	V _{(BR)GSS}	- 25	- 35		V	I _G = - 1 mA, V _{DS} = 0V		
Reverse Gate Leakage Current	I _{GSS}		0.05	0.1	nA	V _{GS} = - 15V, V _{DS} = 0V		
Drain Saturation Current (Pulsed)	I _{DSS}	1		40	mA	V _{DS} = 15V, V _{GS} = 0V		
Gate Source Cutoff Voltage	V _{GS(OFF)}	- 0.5		- 8	V	V _{DS} = 15V, I _D = 1 nA		

Dynamic Electrical Characteristics

Drain Source ON Resistance	r _{ds(on)}	90		250	Ω	I _D = 0 mA, V _{GS} = 0V	f = 1 kHz
Forward Transconductance	g _{fs}		8.5		mS	V _{DS} = 15V, V _{GS} = 0V	f = 1 kHz
Input Capacitance	C _{iss}		5.5	7.0	pF	V _{DS} = 10V, V _{GS} = 0V	f = 1 MHz
Feedback Capacitance	C _{rss}		1.5	3	pF	V _{DS} = 10V, V _{GS} = 0V	f = 1 MHz
Equivalent Noise Voltage	e _N		5		nV/√HZ	V _{DS} = 15V, I _D = 5 mA	f = 1 kHz
Differential Gate Source Voltage	V _{GS1} - V _{GS2}	5	20	100	mV	V _{DG} = 15V, I _D = 5 mA	



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